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November 2013

FDU6N25

N-Channel UniFETTM MOSFET 250 V, 4.4 A, 1.1 Ω

Features

- $R_{DS(on)}$ = 0.9 Ω (Typ.) @ V_{GS} = 10 V, I_D = 2.2 A
- Low Gate Charge (Typ. 4.5 nC)
- Low C_{rss} (Typ. 5 pF)
- 100% Avalanche Tested

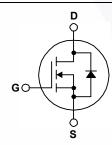
Applications

- LCD/LED/PDP TV
- · Consumer Appliances
- · Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDU6N25	Unit
V _{DSS}	Drain-Source Voltage			250	V
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)			A A
I _{DM}	Drain Current	- Pulsed	(Note 1)	18	Α
V _{GSS}	Gate-Source voltage			±30	V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	12	mJ
I _{AR}	Avalanche Current		(Note 1)	4.4	А
E _{AR}	Repetitive Avalanche Energy		(Note 1)	5	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C			W W/°C
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	FDU6N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	110	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDU6N25	FDU6N25	IPAK	Tube	N/A	N/A	70 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					ı
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.25		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V V _{DS} = 200 V, T _C = 125°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.2 A		0.9	1.1	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 2.2 A		5.5		S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		194	250	pF
C _{oss}	Output Capacitance			38	50	pF
C _{rss}	Reverse Transfer Capacitance			5	8	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V_{DD} = 125 V, I_{D} = 6 A, V_{GS} = 10 V, R_{G} = 25 Ω (Note 4)		10	30	ns
t _r	Turn-On Rise Time			25	60	ns
t _{d(off)}	Turn-Off Delay Time			7	24	ns
t _f	Turn-Off Fall Time			12	34	ns
Qg	Total Gate Charge	$V_{DS} = 200 \text{ V}, I_{D} = 6 \text{ A},$		4.5	6	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V (Note 4)		1.5		nC
Q _{gd}	Gate-Drain Charge			1.8		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				4.4	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				18	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 4.4 A,			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_{S} = 6 \text{ A}$ $dI_{F}/dt = 100 \text{ A}/\mu\text{s}$		145		ns
Q _{rr}	Reverse Recovery Charge			0.55		μС

Notes

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 1.2 mH, I $_{AS}$ = 4.4 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$

^{3.} I $_{SD}$ \leq 4.4 A, di/dt \leq 200 A/µs, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.

^{4.} Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

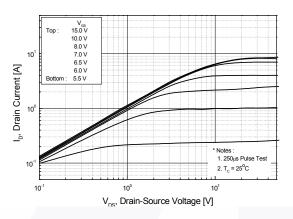


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

Figure 2. Transfer Characteristics

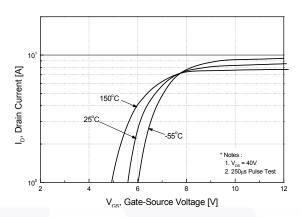


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

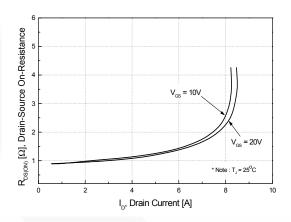
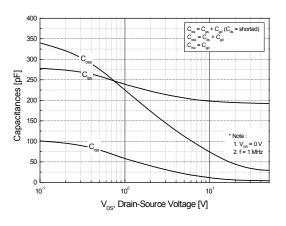
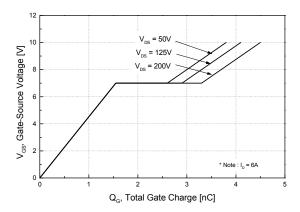


Figure 5. Capacitance Characteristics



To 100 2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0 V_{SD}, Source-Drain voltage [V]

Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

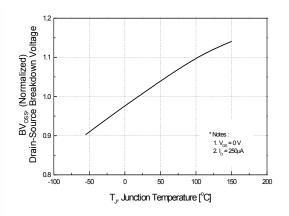


Figure 8. On-Resistance Variation vs. Temperature

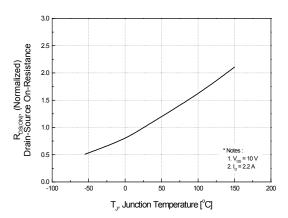


Figure 9. Maximum Safe Operating Area

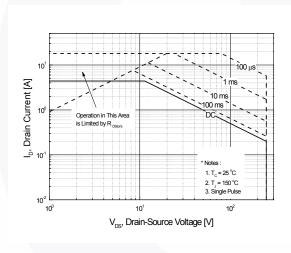


Figure 10. Maximum Drain Current vs. Case Temperature

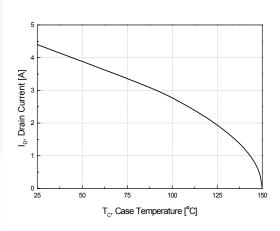
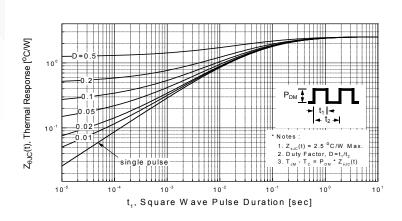


Figure 11. Transient Thermal Response Curve



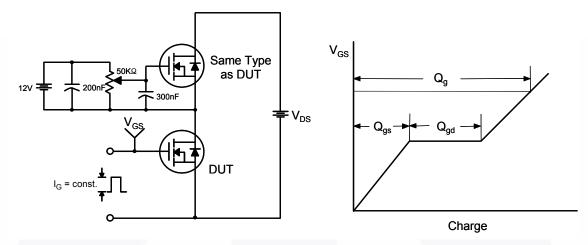


Figure 12. Gate Charge Test Circuit & Waveform

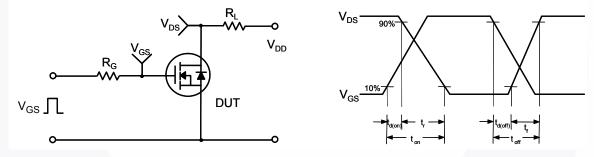


Figure 13. Resistive Switching Test Circuit & Waveforms

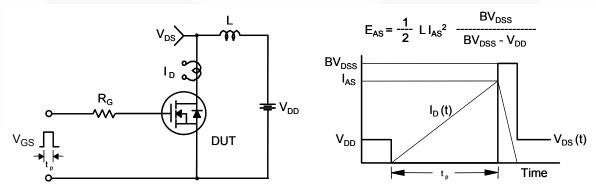


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

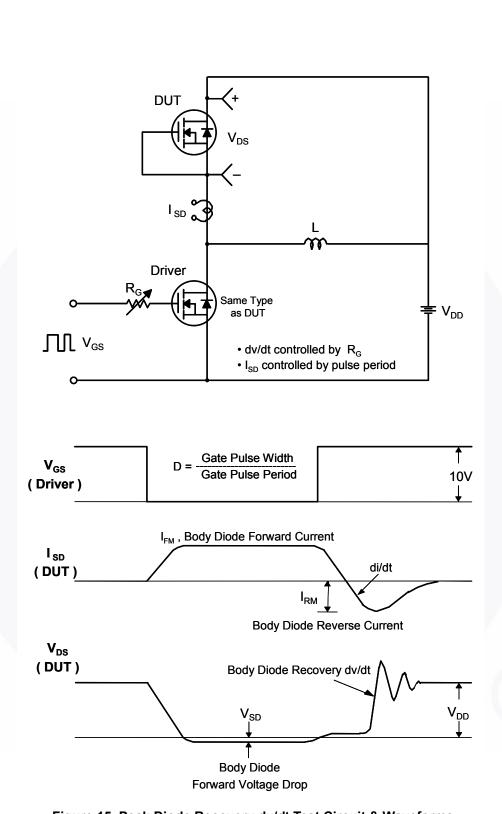
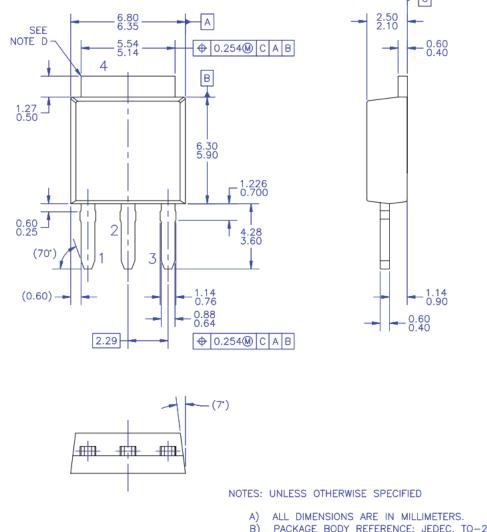


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



- B) PACKAGE BODY REFERENCE: JEDEC, TO-251, ISSUE D, VARIATION AA, DATED JUNE 2002.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) DRAWING FILE NAME: T0251B03_3

Figure 16. TO251 (I-PAK), Molded, 3-Lead (Short Leads), FO71

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